COURSE SYLLABUS AND SCHEDULE

| Week | <u>Dates</u> | <u>Topics</u> | <u>Chapter</u> |
|------|--------------|--|----------------|
| 1 | 1/21, 1/23 | Semiconductor Fundamentals: introduction, carrier modeling | 1 & 2 |
| 2 | 1/28, 1/30 | carrier properties, distributions, and concentrations | 2 |
| 3 | 2/4,2/6^ | carrier action | 3 |
| 4 | 2/11, 2/13 | Metal-Semiconductor Contacts and Schottky Diodes | 14 |
| 5 | 2/18, 2/20 | pn Junction Diode: electrostatics | 5 |
| 6 | 2/25, 2/27^ | <i>I-V</i> characteristics | 6 |
| 7 | 3/4, 3/6 | junction capacitance, transient response | 7 & 8 |
| 8 | 3/11, 3/13^ | Bipolar Junction Transistor: structure and operation | 10 |
| 9 | 3/18, 3/20 | BJT static characteristics | 11 |
| | | (Spring Recess 3/24-3/28) | |
| 10 | 4/1, 4/3^ | BJT dynamic performance | 12 |
| 11 | 4/8,4/10 | Metal-Oxide-Semiconductor Capacitor | (Reader) |
| 12 | 4/15,4/17^ | MOS Field-Effect Transistor: structure and operation | (Reader) |
| 13 | 4/22,4/24* | I-V characteristics | (Reader) |
| 14 | 4/29,5/1 | performance limitations | (Reader) |
| 15 | 5/6, 5/8^ | Advanced transistor structures | (Reader) |
| 16 | 5/13 | Review | |
| | | | |

FINAL EXAM: Friday 5/23, 12:30-3:30 PM

^{*}Design Project Due

[^]Quiz date